

BLL6H1214-500; BLL6H1214LS-500

LDMOS L-band radar power transistor

Rev. 3 — 5 August 2013

Product data sheet

1. Product profile

1.1 General description

500 W LDMOS power transistor intended for L-band radar applications in the 1.2 GHz to 1.4 GHz range.

Table 1. Test information

Typical RF performance at $T_{case} = 25\text{ °C}$; $t_p = 300\text{ }\mu\text{s}$; $\delta = 10\%$; $I_{Dq} = 150\text{ mA}$; in a class-AB production test circuit.

Test signal	f (GHz)	V _{DS} (V)	P _L (W)	G _p (dB)	η_D (%)	t _r (ns)	t _f (ns)
pulsed RF	1.2 to 1.4	50	500	17	50	20	6

1.2 Features and benefits

- Easy power control
- Integrated ESD protection
- High flexibility with respect to pulse formats
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1.2 GHz to 1.4 GHz)
- Internally matched for ease of use
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

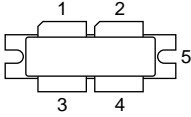
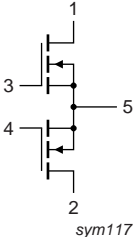
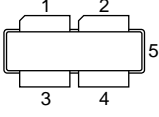
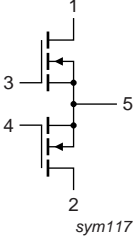
1.3 Applications

- L-band power amplifiers for radar applications in the 1.2 GHz to 1.4 GHz frequency range



2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLL6H1214-500 (SOT539A)			
1	drain1		 sym117
2	drain2		
3	gate1		
4	gate2		
5	source		
BLL6H1214LS-500 (SOT539B)			
1	drain1		 sym117
2	drain2		
3	gate1		
4	gate2		
5	source		

[1] Connected to flange.

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLL6H1214-500	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A
BLL6H1214LS-500	-	earless flanged balanced ceramic package; 4 leads	SOT539B

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	100	V
V_{GS}	gate-source voltage		-0.5	+13	V
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-	200	°C

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Typ	Unit
BLL6H1214-500				
$Z_{th(j-c)}$	transient thermal impedance from junction to case	$T_{case} = 85\text{ °C}; P_L = 500\text{ W}$		
		$t_p = 100\text{ }\mu\text{s}; \delta = 10\text{ }\%$	0.07	K/W
		$t_p = 200\text{ }\mu\text{s}; \delta = 10\text{ }\%$	0.08	K/W
		$t_p = 300\text{ }\mu\text{s}; \delta = 10\text{ }\%$	0.1	K/W
		$t_p = 100\text{ }\mu\text{s}; \delta = 20\text{ }\%$	0.1	K/W
BLL6H1214LS-500				
$Z_{th(j-c)}$	transient thermal impedance from junction to case	$T_{case} = 85\text{ °C}; P_L = 500\text{ W}$		
		$t_p = 100\text{ }\mu\text{s}; \delta = 10\text{ }\%$	0.046	K/W
		$t_p = 200\text{ }\mu\text{s}; \delta = 10\text{ }\%$	0.059	K/W
		$t_p = 300\text{ }\mu\text{s}; \delta = 10\text{ }\%$	0.069	K/W
		$t_p = 100\text{ }\mu\text{s}; \delta = 20\text{ }\%$	0.064	K/W

6. Characteristics

Table 6. DC characteristics

$T_j = 25\text{ °C}$; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 2.7\text{ mA}$	100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 270\text{ mA}$	1.3	1.8	2.2	V
I_{DSS}	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 50\text{ V}$	-	-	1.4	μA
I_{DSX}	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $V_{DS} = 10\text{ V}$	32	42	-	A
I_{GSS}	gate leakage current	$V_{GS} = 11\text{ V}; V_{DS} = 0\text{ V}$	-	-	140	nA
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 270\text{ mA}$	1.7	3	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75\text{ V};$ $I_D = 9.5\text{ A}$	-	100	164	$\text{m}\Omega$

Table 7. RF characteristics

Test signal: pulsed RF; $t_p = 300\text{ }\mu\text{s}$; $\delta = 10\text{ }\%$; RF performance at $V_{DS} = 50\text{ V}$; $I_{Dq} = 150\text{ mA}$; $T_{case} = 25\text{ °C}$; unless otherwise specified, in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
P_L	output power		500	-	-	W
V_{DS}	drain-source voltage	$P_L = 500\text{ W}$	-	-	50	V
G_p	power gain	$P_L = 500\text{ W}$	15	17	-	dB
RL_{in}	input return loss	$P_L = 500\text{ W}$	-	-10	-	dB
$P_{L(1dB)}$	output power at 1 dB gain compression		-	600	-	W
η_D	drain efficiency	$P_L = 500\text{ W}$	45	50	-	%

Table 7. RF characteristics ...continued

Test signal: pulsed RF; $t_p = 300 \mu\text{s}$; $\delta = 10 \%$; RF performance at $V_{DS} = 50 \text{ V}$; $I_{Dq} = 150 \text{ mA}$; $T_{case} = 25 \text{ }^\circ\text{C}$; unless otherwise specified, in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$P_{\text{droop(pulse)}}$	pulse droop power	$P_L = 500 \text{ W}$	-	0	0.3	dB
t_r	rise time	$P_L = 500 \text{ W}$	-	20	50	ns
t_f	fall time	$P_L = 500 \text{ W}$	-	6	50	ns

7. Test information

7.1 Ruggedness in class-AB operation

The BLL6H1214-500 and BLL6H1214LS-500 are capable of withstanding a load mismatch corresponding to $V_{\text{SWR}} = 10 : 1$ through all phases under the following conditions: $V_{DS} = 50 \text{ V}$; $I_{Dq} = 150 \text{ mA}$; $P_L = 500 \text{ W}$; $t_p = 300 \mu\text{s}$; $\delta = 10 \%$.

7.2 Impedance information

Table 8. Typical impedance

Typical values per section unless otherwise specified.

f (GHz)	Z_S (Ω)	Z_L (Ω)
1.2	$1.268 - j2.623$	$2.987 - j1.664$
1.3	$2.193 - j2.457$	$2.162 - j1.326$
1.4	$2.359 - j2.052$	$1.604 - j1.887$

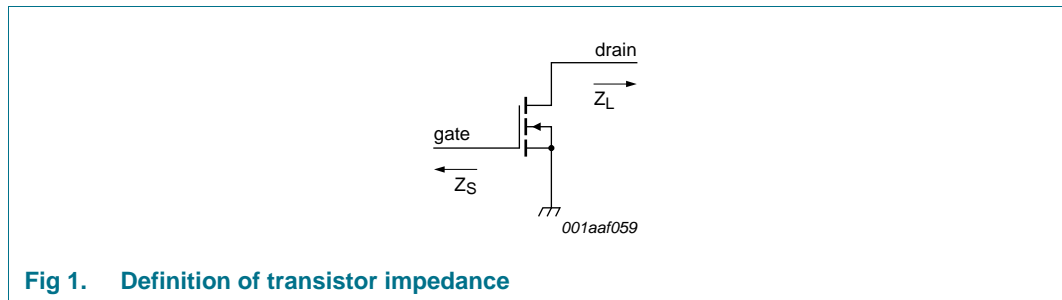


Fig 1. Definition of transistor impedance

7.3 Test circuit

Table 9. List of components

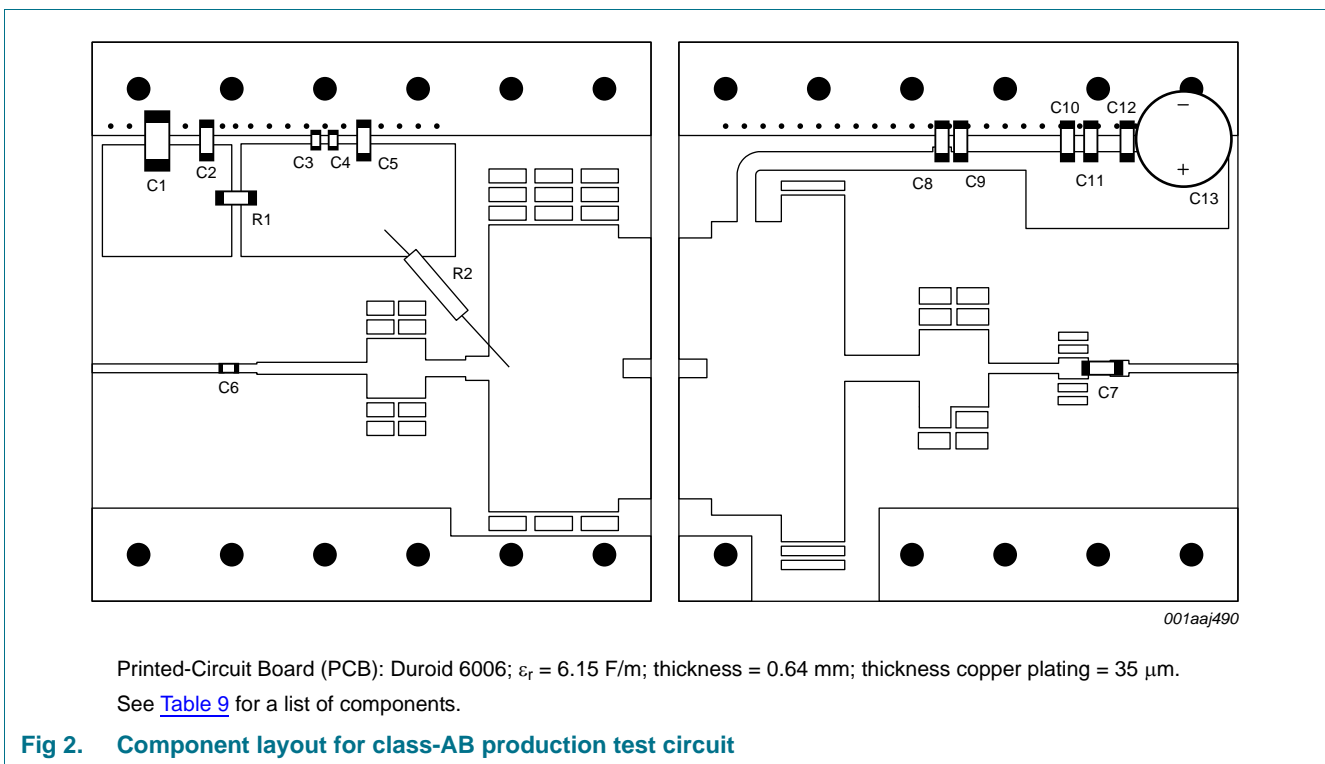
For test circuit see [Figure 2](#).

Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	22 μF , 35 V	
C2	multilayer ceramic chip capacitor	51 pF	[1]
C3, C4	multilayer ceramic chip capacitor	100 pF	[1]
C5, C11, C12	multilayer ceramic chip capacitor	1 nf	[2]
C6	multilayer ceramic chip capacitor	47 pF	[1]
C7, C8, C10	multilayer ceramic chip capacitor	51 pF	[3]

Table 9. List of components ...continued
 For test circuit see [Figure 2](#).

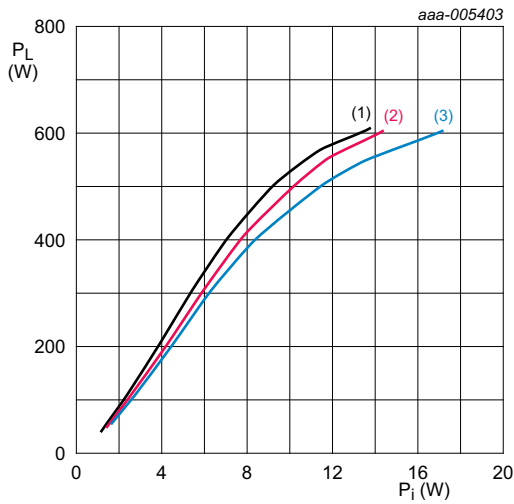
Component	Description	Value	Remarks
C9	multilayer ceramic chip capacitor	100 pF	[3]
C13	electrolytic capacitor	10 μ F, 63 V	
R1	SMD resistor	56 Ω	0603
R2	metal film resistor	51 Ω	

- [1] American Technical Ceramics type 100A or capacitor of same quality.
- [2] American Technical Ceramics type 100B or capacitor of same quality.
- [3] American Technical Ceramics type 800B or capacitor of same quality.



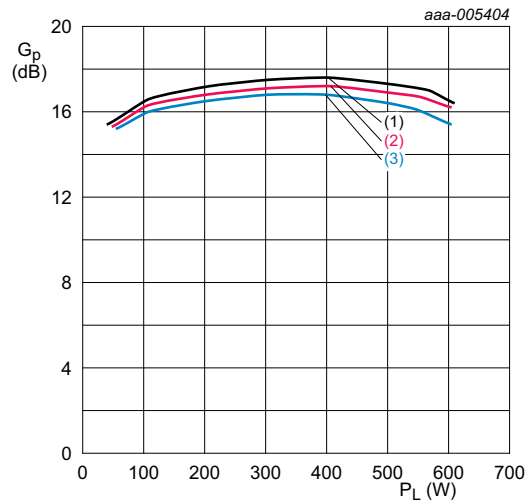
7.4 RF performance graphs

7.4.1 Performance curves measured with $\delta = 10\%$, $t_p = 300 \mu s$ and $T_h = 25^\circ C$



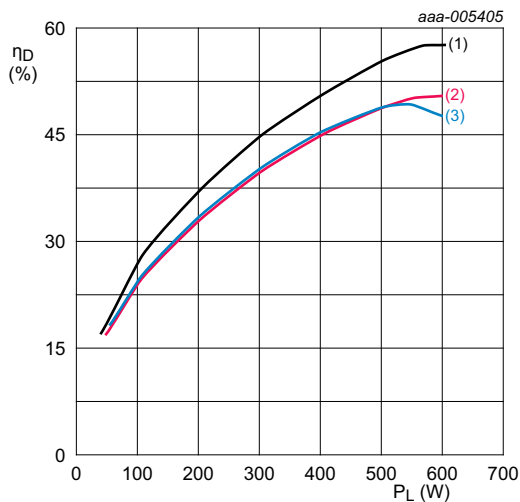
$V_{DS} = 50 V$; $I_{Dq} = 150 mA$.
 (1) $f = 1200 MHz$
 (2) $f = 1300 MHz$
 (3) $f = 1400 MHz$

Fig 3. Output power as a function of input power; typical values



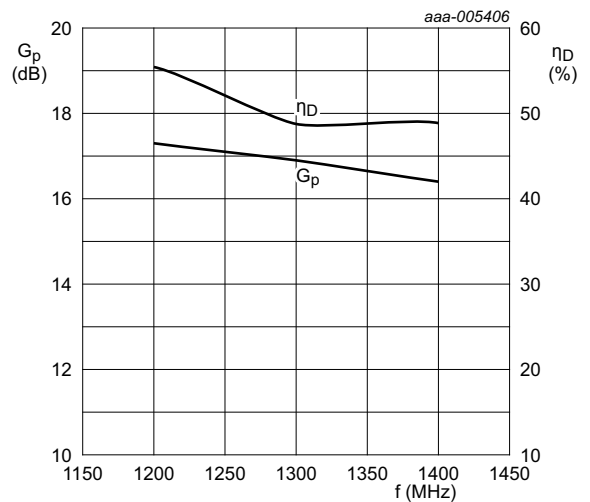
$V_{DS} = 50 V$; $I_{Dq} = 150 mA$.
 (1) $f = 1200 MHz$
 (2) $f = 1300 MHz$
 (3) $f = 1400 MHz$

Fig 4. Power gain as a function of output power; typical values



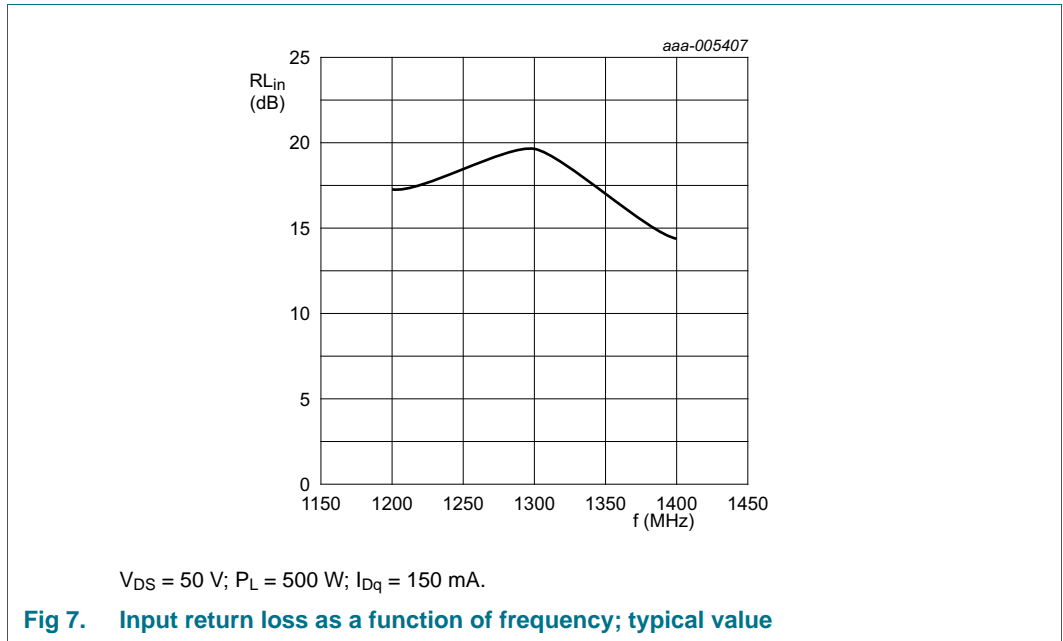
$V_{DS} = 50 V$; $I_{Dq} = 150 mA$.
 (1) $f = 1200 MHz$
 (2) $f = 1300 MHz$
 (3) $f = 1400 MHz$

Fig 5. Drain efficiency as a function of output power; typical values

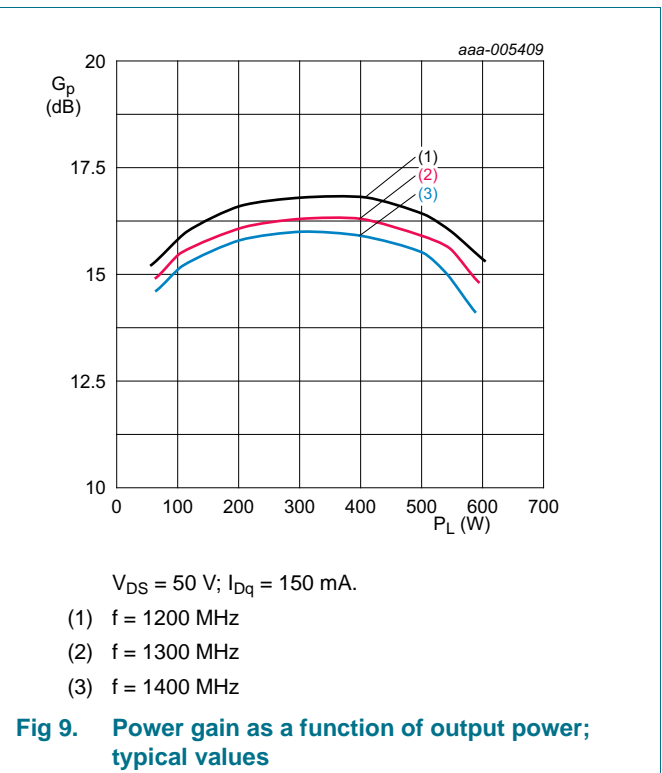
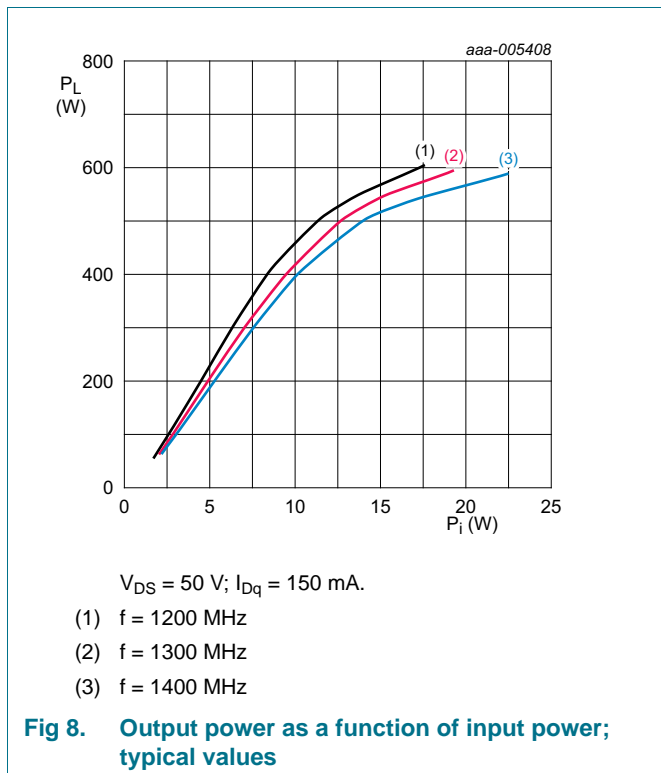


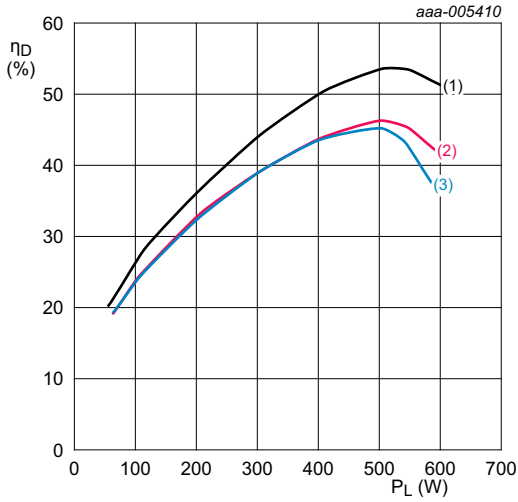
$V_{DS} = 50 V$; $P_L = 500 W$; $I_{Dq} = 150 mA$.

Fig 6. Power gain and drain efficiency as function of frequency; typical values



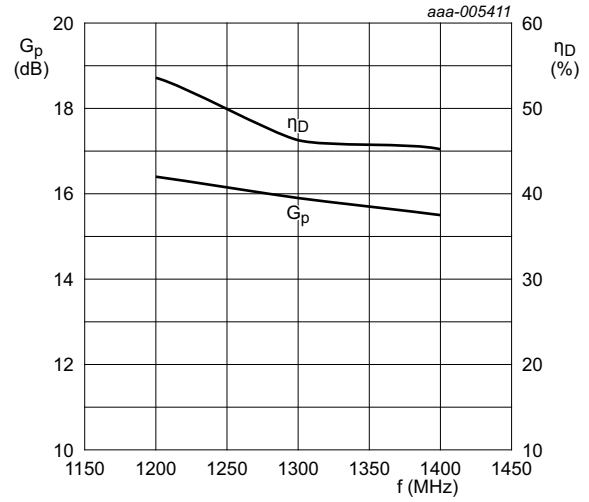
7.4.2 Performance curves measured with $\delta = 10\%$, $t_p = 300\ \mu\text{s}$ and $T_h = 65\ ^\circ\text{C}$





$V_{DS} = 50\text{ V}; I_{Dq} = 100\text{ mA}$.
 (1) $f = 1200\text{ MHz}$
 (2) $f = 1300\text{ MHz}$
 (3) $f = 1400\text{ MHz}$

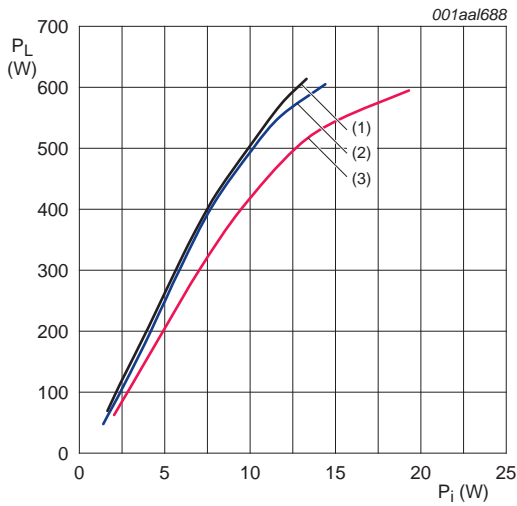
Fig 10. Drain efficiency as a function of output power; typical values



$V_{DS} = 50\text{ V}; P_L = 500\text{ W}; I_{Dq} = 100\text{ mA}$.

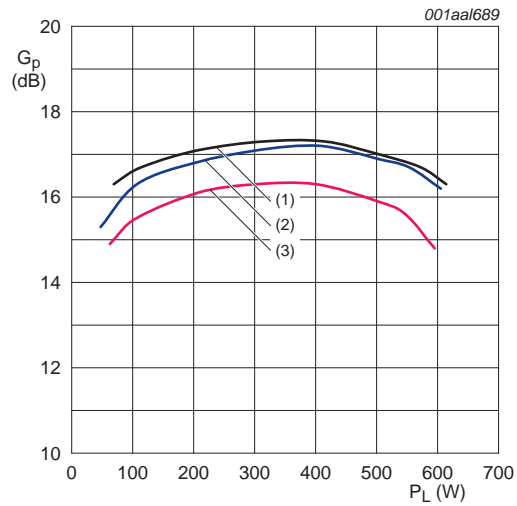
Fig 11. Power gain and drain efficiency as function of frequency; typical values

7.4.3 Performance curves measured with $\delta = 10\%$, $t_p = 300\ \mu\text{s}$ and $f = 1300\text{ MHz}$



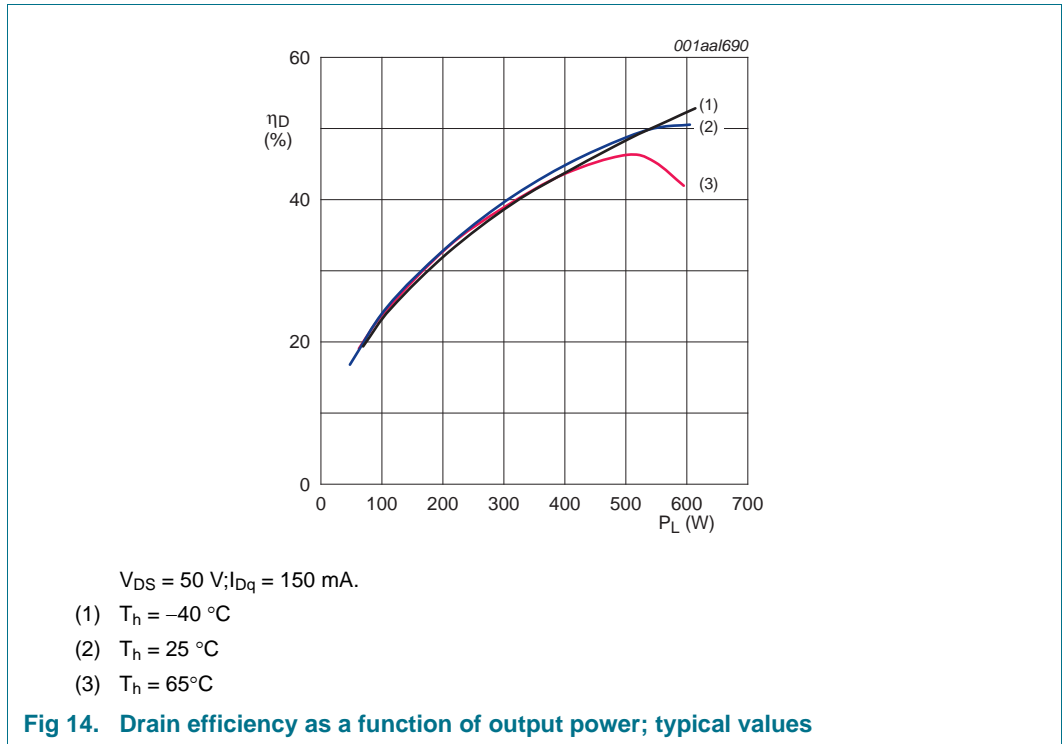
$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}$.
 (1) $T_h = -40^\circ\text{C}$
 (2) $T_h = 25^\circ\text{C}$
 (3) $T_h = 65^\circ\text{C}$

Fig 12. Output power as a function of input power; typical values

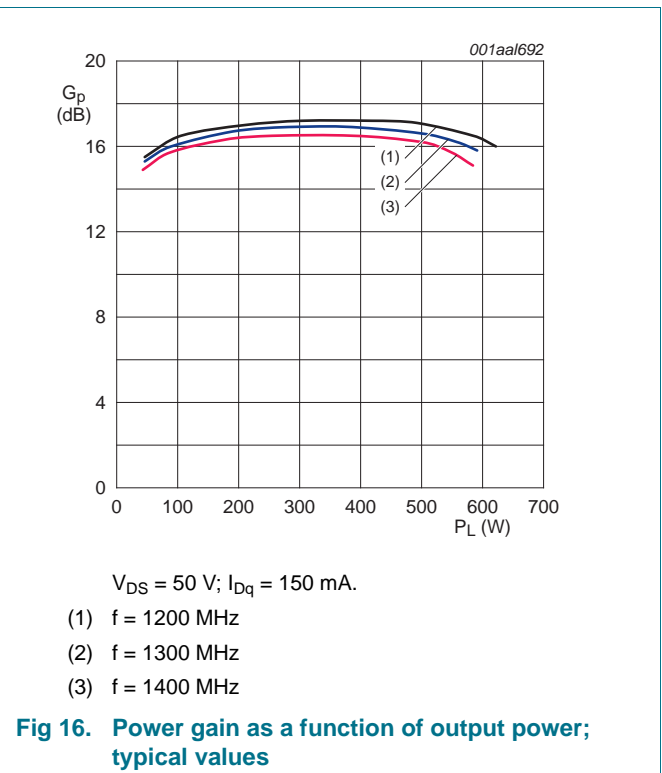
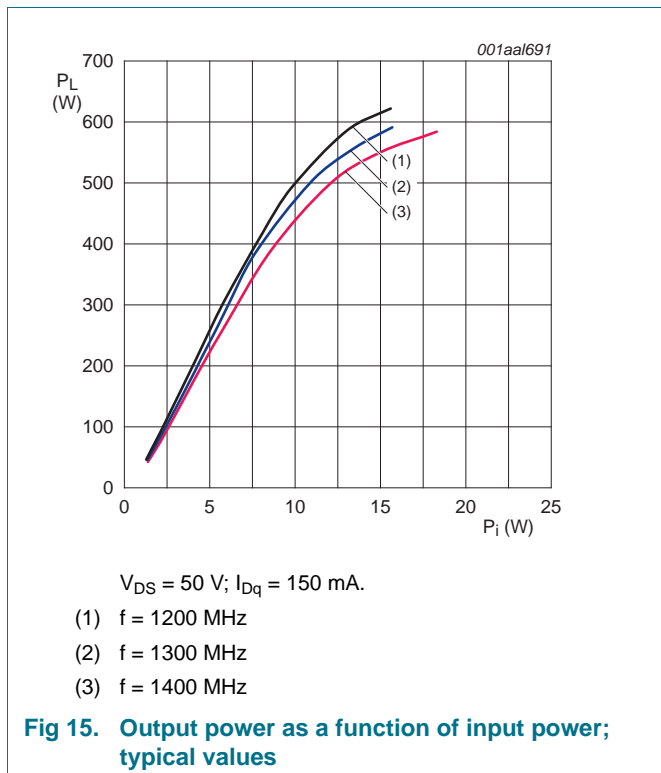


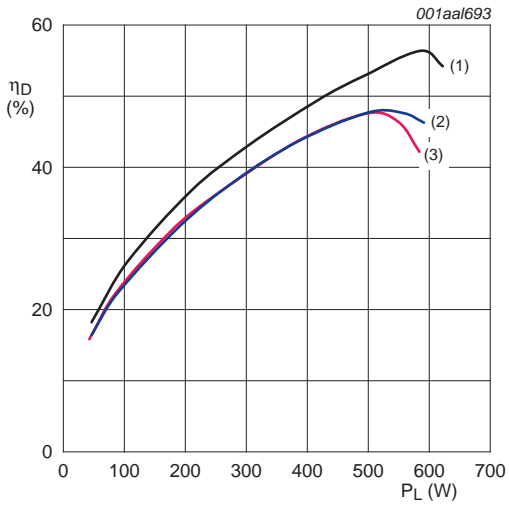
$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}$.
 (1) $T_h = -40^\circ\text{C}$
 (2) $T_h = 25^\circ\text{C}$
 (3) $T_h = 65^\circ\text{C}$

Fig 13. Power gain as a function of output power; typical values



7.4.4 Performance curves measured with $\delta = 20\%$, $t_p = 500\ \mu\text{s}$ and $T_h = 25\text{ }^\circ\text{C}$

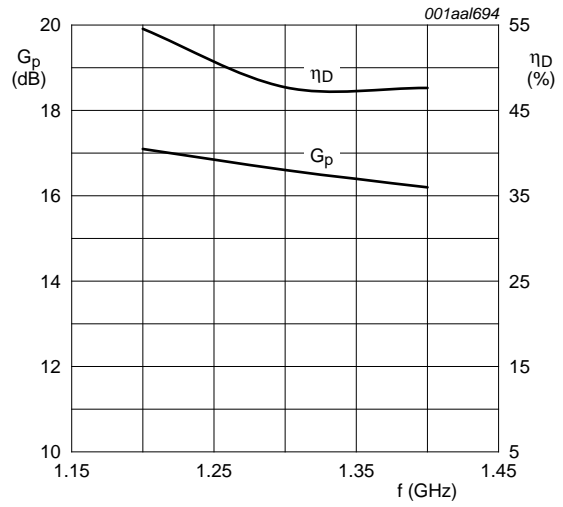




$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}$.

- (1) $f = 1200\text{ MHz}$
- (2) $f = 1300\text{ MHz}$
- (3) $f = 1400\text{ MHz}$

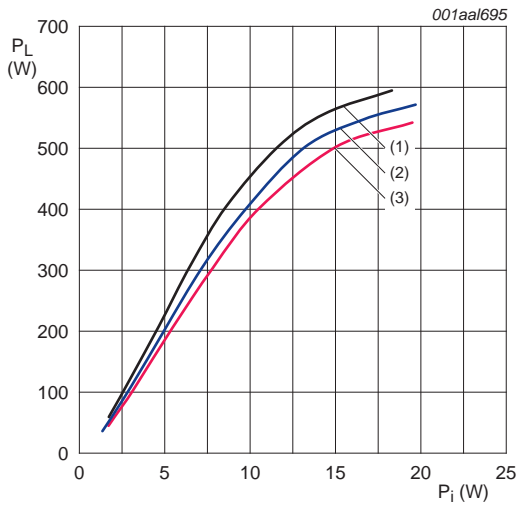
Fig 17. Drain efficiency as a function of output power; typical values



$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}$.

Fig 18. Power gain and drain efficiency as function of frequency; typical values

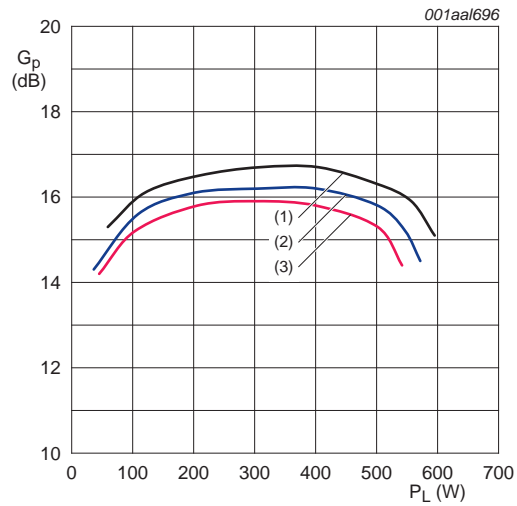
7.4.5 Performance curves measured with $\delta = 20\%$, $t_p = 500\ \mu\text{s}$ and $T_h = 65\text{ }^\circ\text{C}$



$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}$.

- (1) $f = 1200\text{ MHz}$
- (2) $f = 1300\text{ MHz}$
- (3) $f = 1400\text{ MHz}$

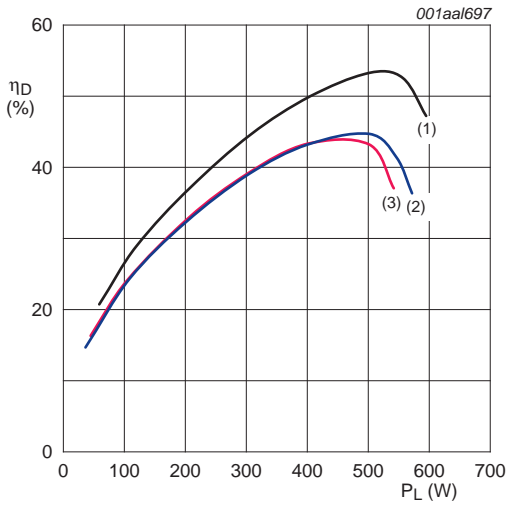
Fig 19. Output power as a function of input power; typical values



$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}$.

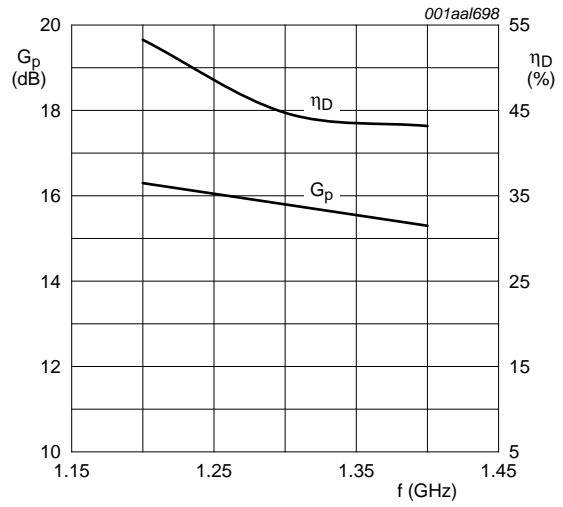
- (1) $f = 1200\text{ MHz}$
- (2) $f = 1300\text{ MHz}$
- (3) $f = 1400\text{ MHz}$

Fig 20. Power gain as a function of output power; typical values



$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$
 (1) $f = 1200\text{ MHz}$
 (2) $f = 1300\text{ MHz}$
 (3) $f = 1400\text{ MHz}$

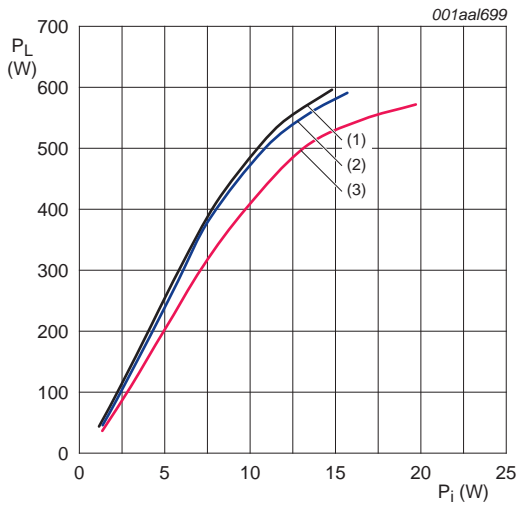
Fig 21. Drain efficiency as a function of output power; typical values



$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$

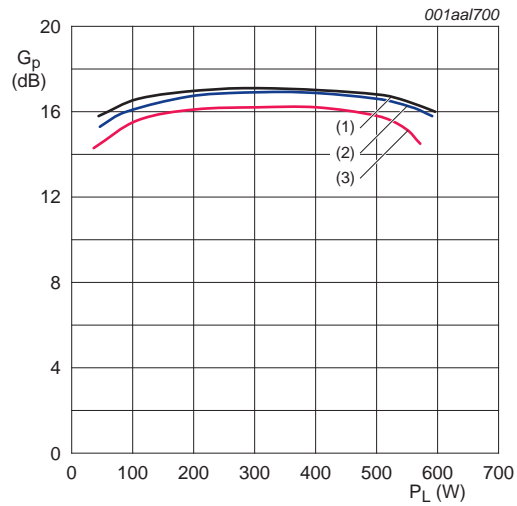
Fig 22. Power gain and drain efficiency as function of frequency; typical values

7.4.6 Performance curves measured with $\delta = 20\%$, $t_p = 500\ \mu\text{s}$ and $f = 1300\text{ MHz}$



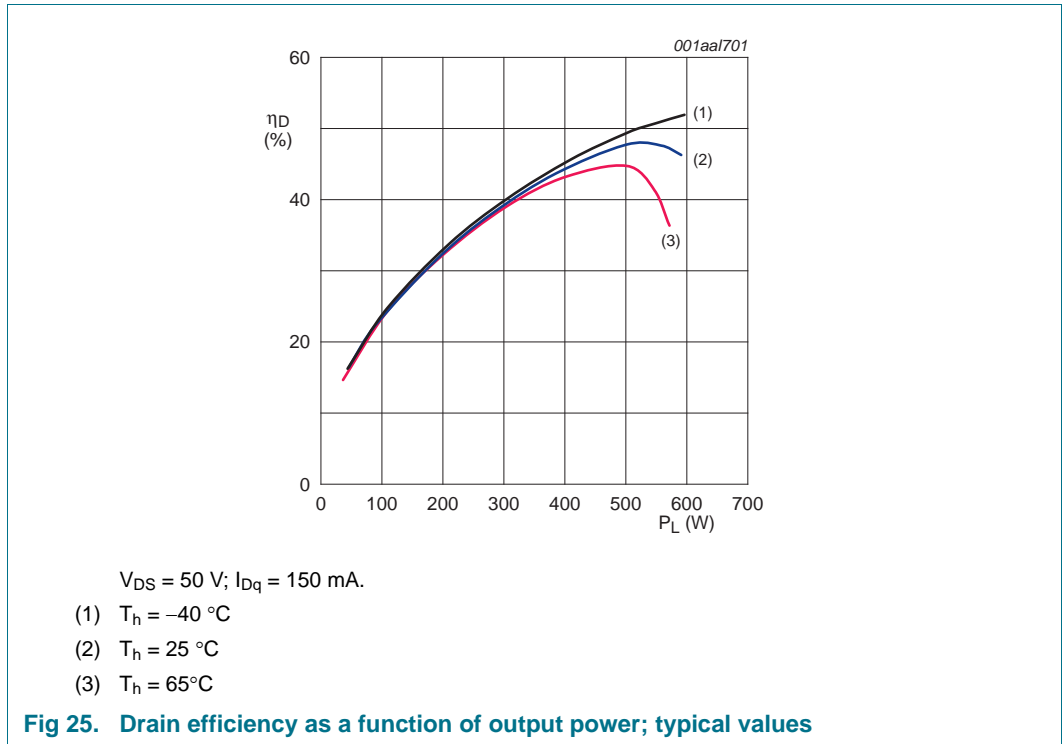
$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$
 (1) $T_h = -40^\circ\text{C}$
 (2) $T_h = 25^\circ\text{C}$
 (3) $T_h = 65^\circ\text{C}$

Fig 23. Output power as a function of input power; typical values

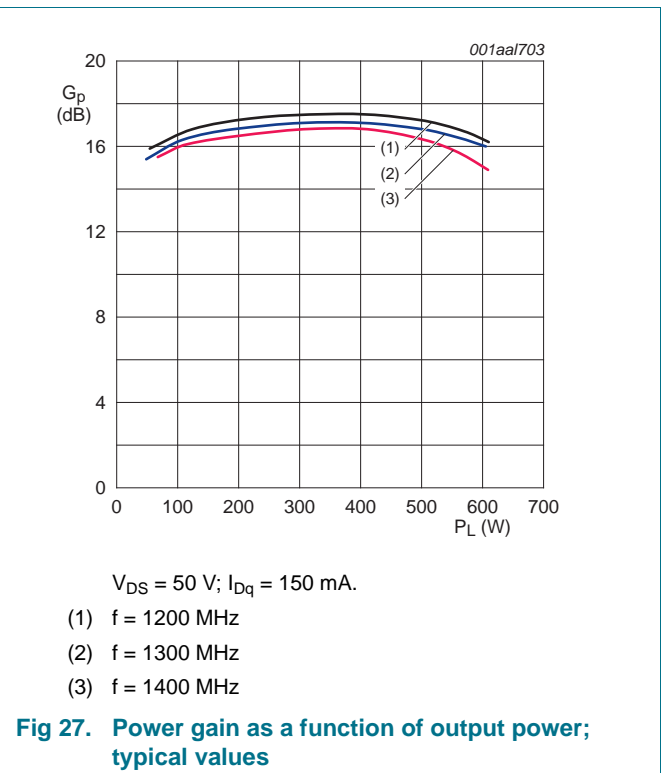
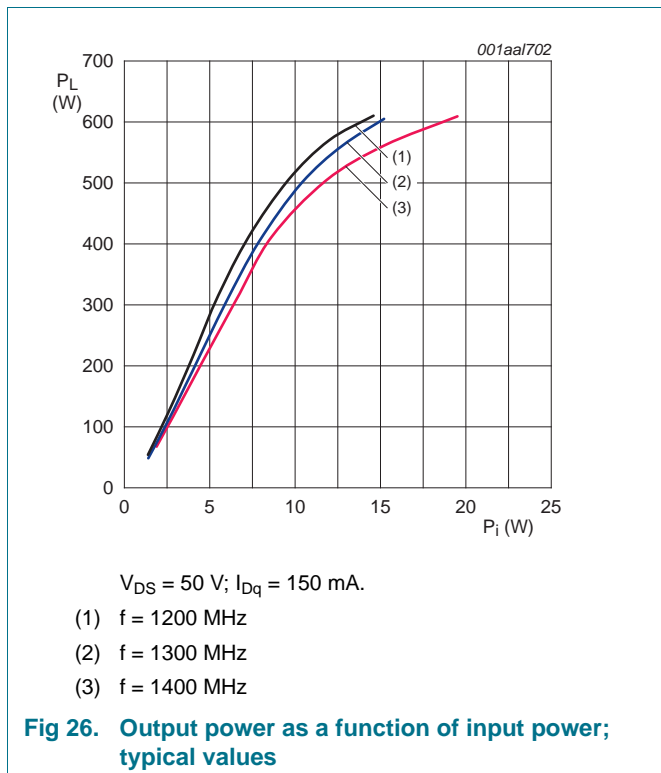


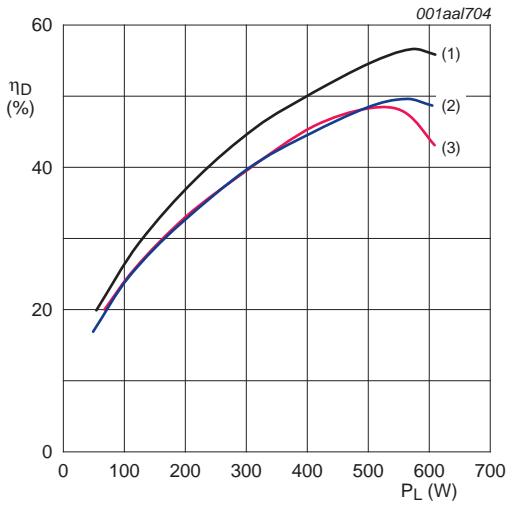
$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$
 (1) $T_h = -40^\circ\text{C}$
 (2) $T_h = 25^\circ\text{C}$
 (3) $T_h = 65^\circ\text{C}$

Fig 24. Power gain as a function of output power; typical values



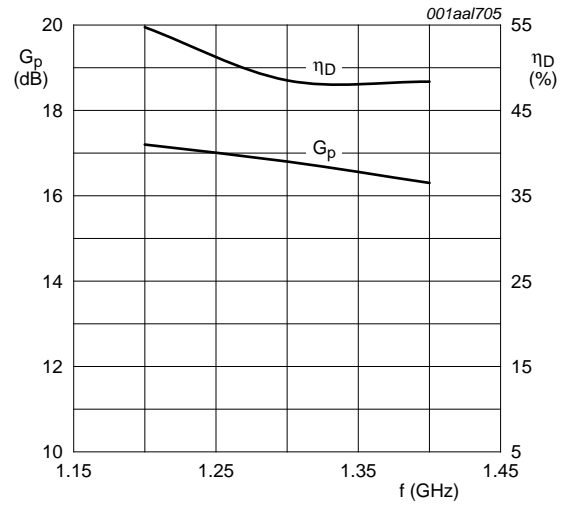
7.4.7 Performance curves measured with $\delta = 10 \%$, $t_p = 1 \text{ ms}$ and $T_h = 25 \text{ }^\circ\text{C}$





$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$
 (1) $f = 1200\text{ MHz}$
 (2) $f = 1300\text{ MHz}$
 (3) $f = 1400\text{ MHz}$

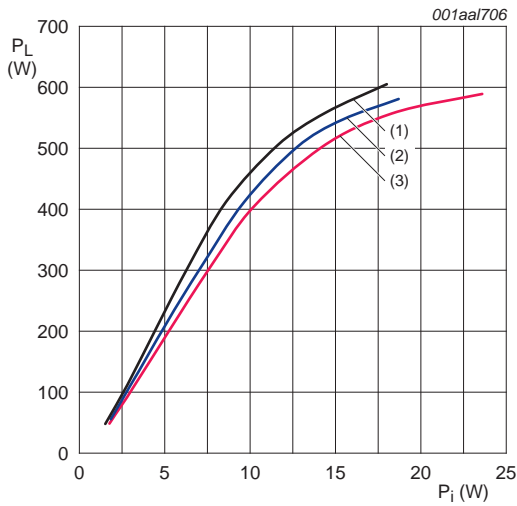
Fig 28. Drain efficiency as a function of output power; typical values



$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$

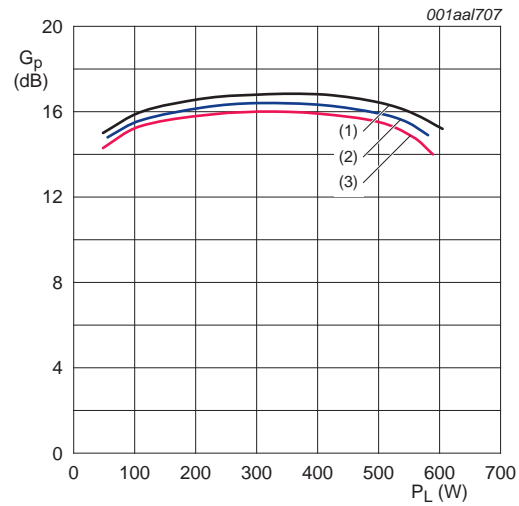
Fig 29. Power gain and drain efficiency as function of frequency; typical values

7.4.8 Performance curves measured with $\delta = 10\%$, $t_p = 1\text{ ms}$ and $T_h = 65\text{ }^\circ\text{C}$



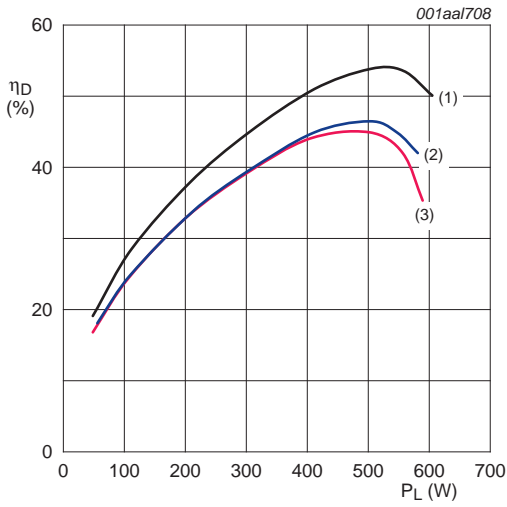
$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$
 (1) $f = 1200\text{ MHz}$
 (2) $f = 1300\text{ MHz}$
 (3) $f = 1400\text{ MHz}$

Fig 30. Output power as a function of input power; typical values



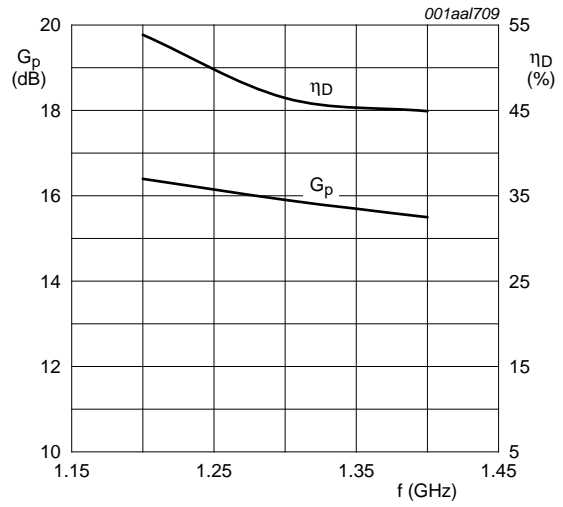
$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$
 (1) $f = 1200\text{ MHz}$
 (2) $f = 1300\text{ MHz}$
 (3) $f = 1400\text{ MHz}$

Fig 31. Power gain as a function of output power; typical values



$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$
 (1) $f = 1200\text{ MHz}$
 (2) $f = 1300\text{ MHz}$
 (3) $f = 1400\text{ MHz}$

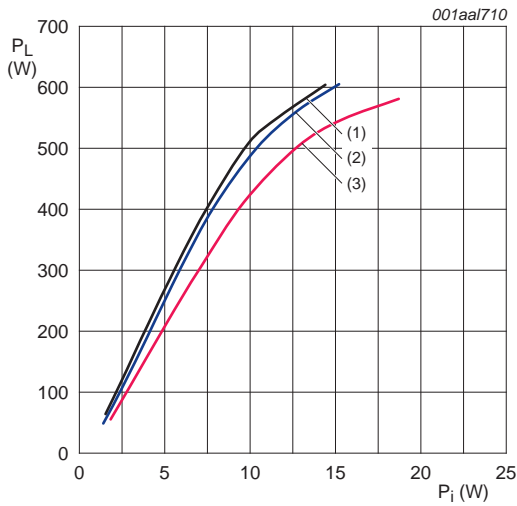
Fig 32. Drain efficiency as a function of output power; typical values



$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$

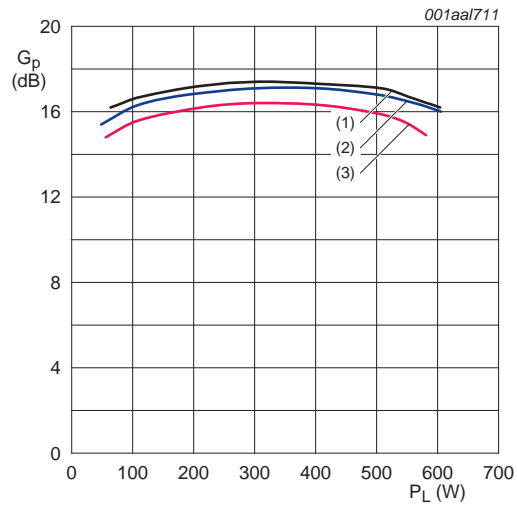
Fig 33. Power gain and drain efficiency as function of frequency; typical values

7.4.9 Performance curves measured with $\delta = 10\%$, $t_p = 1\text{ ms}$ and $f = 1300\text{ MHz}$



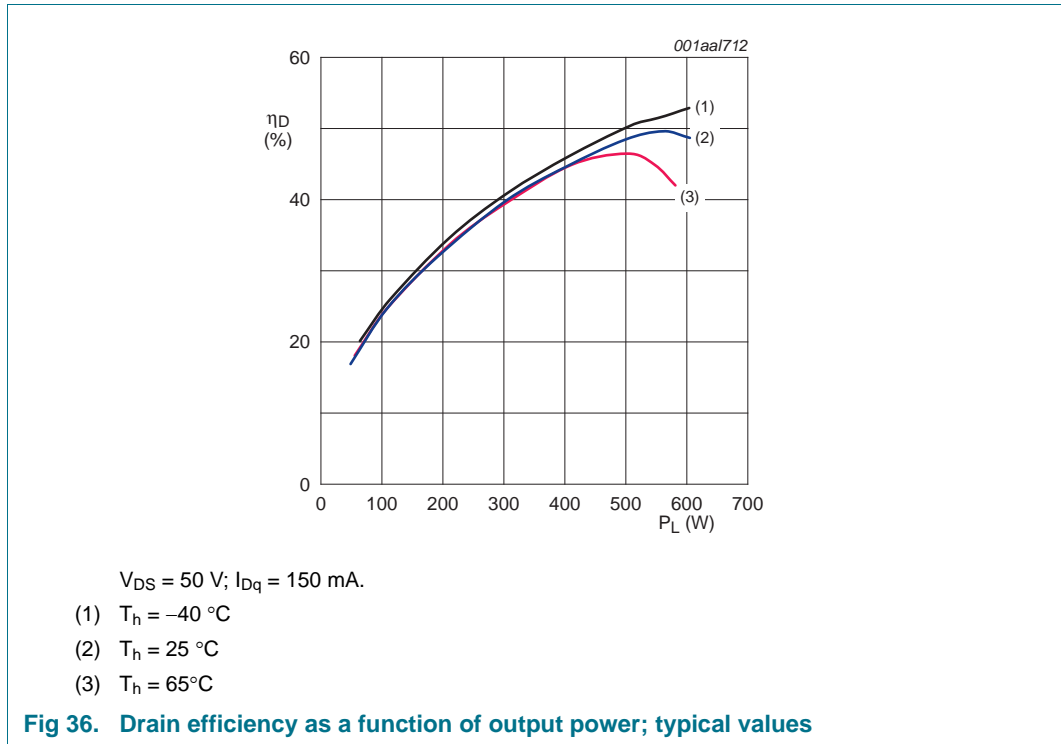
$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$
 (1) $T_h = -40\text{ °C}$
 (2) $T_h = 25\text{ °C}$
 (3) $T_h = 65\text{ °C}$

Fig 34. Output power as a function of input power; typical values



$V_{DS} = 50\text{ V}; I_{Dq} = 150\text{ mA}.$
 (1) $T_h = -40\text{ °C}$
 (2) $T_h = 25\text{ °C}$
 (3) $T_h = 65\text{ °C}$

Fig 35. Power gain as a function of output power; typical values



8. Package outline

Flanged balanced ceramic package; 2 mounting holes; 4 leads

SOT539A

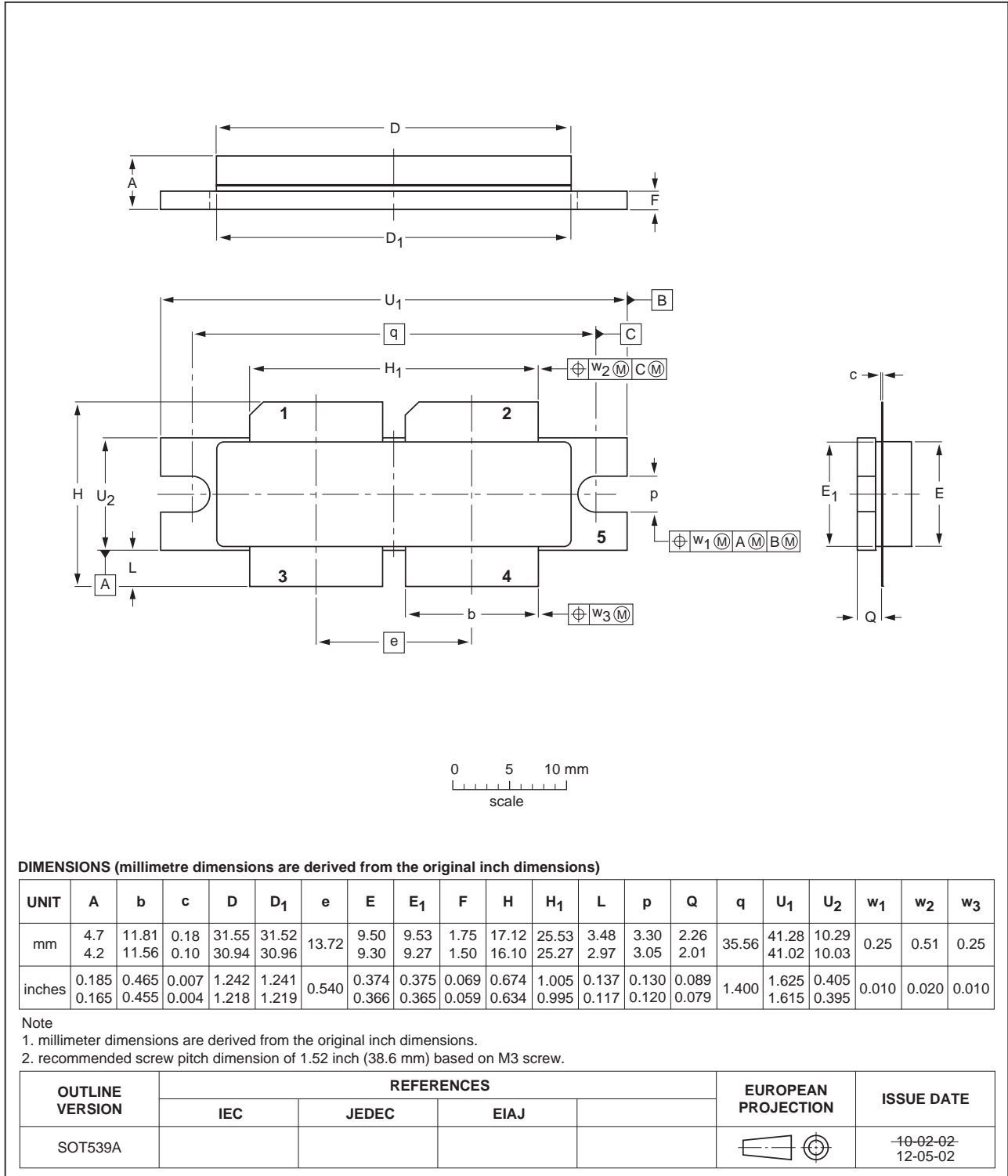


Fig 37. Package outline SOT539A

Earless flanged balanced ceramic package; 4 leads

SOT539B

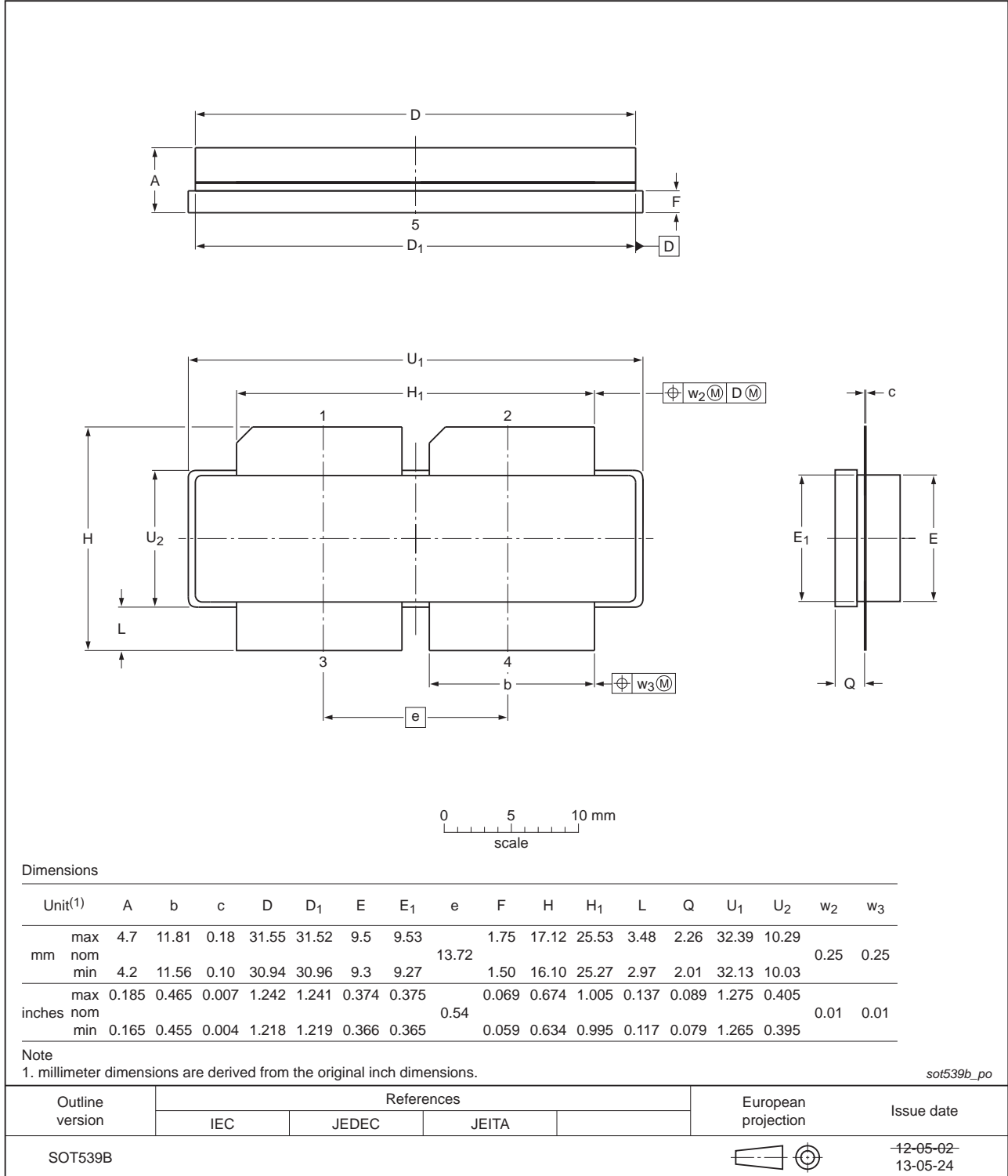


Fig 38. Package outline SOT539B

9. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the *ANSI/ESD S20.20*, *IEC/ST 61340-5*, *JESD625-A* or equivalent standards.

10. Abbreviations

Table 10. Abbreviations

Acronym	Description
ESD	ElectroStatic Discharge
L-band	Long wave Band
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLL6H1214-500_1214LS-500 v.3	20130805	Product data sheet	-	BLL6H1214-500 v.2
Modifications:		<ul style="list-style-type: none"> This document now describes both the BLL6H1214-500 and BLL6H1214LS-500 products. Table 1 on page 1: 'mode of operation' changed to 'test signal'. Table 4 on page 2: removed row 'I_D'. Table 7 on page 3: 'mode of operation' changed to 'test signal'. Section 7 on page 4: moved several sections to this section. Section 7.4 on page 6: updated figure notes. Section 7.4.1 on page 6: updated graphs. Section 7.4.2 on page 7: updated graphs. Figure 38 on page 17: updated figure. 		
BLL6H1214-500 v.2	20100401	Product data sheet	-	BLL6H1214-500 v.1
BLL6H1214-500 v.1	20090120	Objective data sheet	-	-

12. Legal information

12.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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14. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
2	Pinning information	2
3	Ordering information	2
4	Limiting values	2
5	Thermal characteristics	3
6	Characteristics	3
7	Test information	4
7.1	Ruggedness in class-AB operation	4
7.2	Impedance information	4
7.3	Test circuit	4
7.4	RF performance graphs	6
7.4.1	Performance curves measured with $\delta = 10\%$, $t_p = 300\ \mu\text{s}$ and $T_h = 25\ ^\circ\text{C}$	6
7.4.2	Performance curves measured with $\delta = 10\%$, $t_p = 300\ \mu\text{s}$ and $T_h = 65\ ^\circ\text{C}$	7
7.4.3	Performance curves measured with $\delta = 10\%$, $t_p = 300\ \mu\text{s}$ and $f = 1300\ \text{MHz}$	8
7.4.4	Performance curves measured with $\delta = 20\%$, $t_p = 500\ \mu\text{s}$ and $T_h = 25\ ^\circ\text{C}$	9
7.4.5	Performance curves measured with $\delta = 20\%$, $t_p = 500\ \mu\text{s}$ and $T_h = 65\ ^\circ\text{C}$	10
7.4.6	Performance curves measured with $\delta = 20\%$, $t_p = 500\ \mu\text{s}$ and $f = 1300\ \text{MHz}$	11
7.4.7	Performance curves measured with $\delta = 10\%$, $t_p = 1\ \text{ms}$ and $T_h = 25\ ^\circ\text{C}$	12
7.4.8	Performance curves measured with $\delta = 10\%$, $t_p = 1\ \text{ms}$ and $T_h = 65\ ^\circ\text{C}$	13
7.4.9	Performance curves measured with $\delta = 10\%$, $t_p = 1\ \text{ms}$ and $f = 1300\ \text{MHz}$	14
8	Package outline	16
9	Handling information	18
10	Abbreviations	18
11	Revision history	18
12	Legal information	19
12.1	Data sheet status	19
12.2	Definitions	19
12.3	Disclaimers	19
12.4	Trademarks	20
13	Contact information	20
14	Contents	21

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